

L Number	Hits	Search Text	DB	Time stamp
2	13	((("257/314-322,390,391").CCLS.) and wells and @pd > 20010917 not dram	USPAT	2002/06/04 09:56
3	3	((("257/314-322,390,391").CCLS.) and wells not dram) and @ad < 19980820 and @pd > 20010917	USPAT	2002/06/04 09:57
4	48	((("257/314-322,390,391").CCLS.) and (ONO with oxide) and @pd > 20010917	USPAT	2002/06/04 10:01
5	175	((("257/314-322,390,391").CCLS.) not dram) and (((insulation nitride dielectric oxide) adj layers) with floating)	USPAT	2002/06/04 10:04
6	14	((("257/314-322,390,391").CCLS.) not dram) and peripheral and logic and @pd > 20010917	USPAT	2002/06/04 10:05
8	115	((("257/314-322,390,391").CCLS.) not dram) and insulat\$3 and @pd > 20010917	USPAT	2002/06/04 10:05
9	38	((("257/314-322,390,391").CCLS.) not dram) and (insulation dielectric oxide) adj layers and @pd > 20010917	USPAT	2002/06/04 10:07
13	33	((("5748536" "6144064" "6103573" "5907172" "6157060" "5969383" "5939749" "50485987" "80242807" "620408732" "5309371" "09321156" "11074389" "07142617" "07147336" "09321157" "2000188344").pn.)	USPAT;	2002/06/04 09:57
-	150	((("257/314-322,390,391").CCLS.) and wells not dram) and @pd < 19980820	US-PGPUB;	2002/06/03 18:55
-	1	03219496.pn.	EPO; JPO;	2002/06/02 17:28
-	251	((("257/314-322,390,391").CCLS.) and peripheral and logic	DERWENT;	2001/09/17 18:11
-	63	((("257/314-322,390,391").CCLS.) and peripheral with logic	IBM_TDB	2001/09/17 18:04
-	3364	((("257/314-322,390,391").CCLS.) not dram	USPAT;	2002/06/04 10:04
-	211	((("257/314-322,390,391").CCLS.) not dram) and peripheral and logic	US-PGPUB;	2002/06/04 16:63
-	44	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic	EPO; JPO;	2001/09/17 18:11
-	15	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic) and eeprom	DERWENT;	2002/06/04 10:05
-	704	((("257/314-322,390,391").CCLS.) not dram) and insulation	IBM_TDB	2001/09/17 18:18
-	2449	((("257/314-322,390,391").CCLS.) not dram) and (insulation dielectric oxide)	USPAT;	
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

524	((("257/314-322,390,391").CCLS.) not dram) and (insulation dielectric oxide) adj layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 10:05
169	((("257/314-322,390,391").CCLS.) not dram) and ((insulation nitride dielectric oxide) adj layers) with floating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 10:03
43	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic and regions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 19:48
39	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic and regions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 19:48
25	((("257/314-322,390,391").CCLS.) and (ONO with oxide) and @pd < 19940101	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 10:00
6	((("257/314-322,390,391").CCLS.) and @pd > 20010914 and @ad < 19990820) and peripheral and logic	USPAT	2002/06/02 17:29
2483	(257/314-322,390,391).CCLS.	USPAT	2002/06/02 17:27
272	((("257/314-322,390,391").CCLS.) and wells	USPAT	2002/06/04 08:17